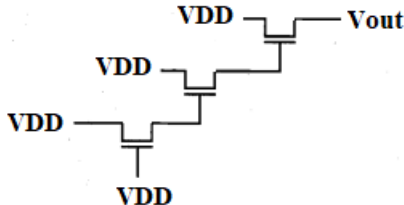
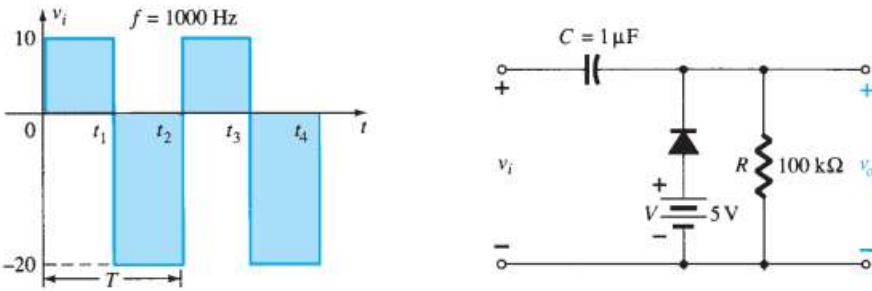


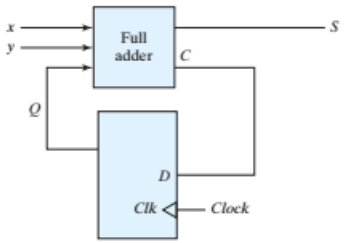
**EVEN SEMESTER EXAMINATION, 2023 – 24**  
**3<sup>rd</sup> yr B.Tech. – Electronics & Communication Engineering**  
**CMOS Design**

Duration: 3:00 hrs

Max Marks: 100

*Note: - Attempt all questions. All Questions carry equal marks. In case of any ambiguity or missing data, the same may be assumed and state the assumption made in the answer.*

Q 1.	<p>Answer any four parts of the following.</p> <ol style="list-style-type: none"> <li>Discuss the VLSI design flow.</li> <li>Define the terms regularity, modularity, and locality.</li> <li>What is CMOS n-well process?</li> <li>Explain LOCOS technique and its importance in fabrication process.</li> <li>Mention the short-channel effects in ultra-nanoscale regime.</li> <li>Discuss the MOSIS layout design rules in detail.</li> </ol>	5x4=20
Q 2.	<p>Answer any four parts of the following.</p> <ol style="list-style-type: none"> <li>Calculate the <math>V_{out}</math>, as shown in figure if <math>V_{DD}</math> is 5V and threshold voltage of each device is 1V.</li> </ol>  <ol style="list-style-type: none"> <li>Write a SPICE netlist for a CMOS inverter.</li> <li>Explain Mealy and Moore machines with examples.</li> <li>Sketch the transfer characteristics of a <math>p</math>-channel enhancement-type MOSFET if threshold voltage is -5 V and <math>k = 0.45 \times 10^{-3} \text{ A/V}^2</math>.</li> <li>Design 3-input NAND gate using CMOS logic.</li> <li>Derive the expression of output impedance for CE configured BJT using hybrid parameter model.</li> </ol>	5x4=20
Q 3.	<p>Answer any two parts of the following.</p> <ol style="list-style-type: none"> <li>Define the complete IC fabrication flow in details with schematics.</li> <li>Explain the working of Czochralski crystal growth process with diagrams.</li> <li>Determine <math>v_o</math> for the network, as shown in the figure for the input indicated.</li> </ol> 	10x2= 20
Q 4.	<p>Answer any two parts of the following.</p> <ol style="list-style-type: none"> <li>Design a 101 sequence detector using Moore's non-overlapping method.</li> </ol>	10x2= 20

	<p>b) What are the different CVD methods? Details the APCVD method.</p> <p>c) A sequential circuit has one flip-flop, two inputs <math>x</math> and <math>y</math>, and one output <math>S</math>. It consists of a full-adder circuit connected to a D flip-flop, as shown in figure. Derive the state table and state diagram of the sequential circuit.</p> 	
Q 5.	<p>Answer any two parts of the following.</p> <p>a) Write the IC production steps in detail.</p> <p>b) Derive the formula for junction depth for pre-deposition case of Fick's second law.</p> <p>c) A synchronous Moore FSM has a single input, <math>x_{in}</math>, and a single output <math>y_{out}</math>. The machine is to monitor the input and remain in its initial state until a second sample of <math>x_{in}</math> is detected to be 1. Upon detecting the second assertion of <math>x_{in}</math> <math>y_{out}</math> is to asserted and remain asserted until a fourth assertion of <math>x_{in}</math> is detected. When the fourth assertion of <math>x_{in}</math> is detected the machine is to return to its initial state and resume monitoring of <math>x_{in}</math>. Draw the state diagram of the machine.</p>	10x2= 20

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